

3.020 Lecture 18

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1 Estimating properties of reacting gas systems

Consider reaction $A + B \longleftrightarrow 2C$

Q. What can we learn from plots of free energy v.s. composition ?

$$G' = \sum_i n_i \mu_i = \sum_i n_i \mu_i^0 + \sum_i n_i RT \ln(P_i/P)$$

n_i : composition

μ_i^0 : chem. potential at pure component i at pressure P

$RT, \ln(P_i/P)$: system at fixed T and P

- Univariant reacting system \rightarrow composition can be expressed in terms of a single variable

– write w.r.t. n_c

$$dn_A = dn_B = -\frac{1}{2}dn_c$$

$$n_A = n_{A,i} + \int dn_A = n_{A,i} - \frac{1}{2}(n_C - n_{C,i})$$

$$n_B = n_{B,i} + \int dn_B = n_{B,i} - \frac{1}{2}(n_C - n_{C,i})$$

$$n_c = n_c \quad \text{constant for this particular rx'n, not so in general}$$

– also need $n_{TOT} = n_A + n_B + n_C = n_{A,i} + n_{B,i} + n_{C,i}$ to write

$$P_i = P \frac{n_i}{n_{TOT}}$$

- now can write out $G'(n_C)$ and plot

$$G' = (n_{A,i} - \frac{1}{2}(n_C - n_{C,i})) \mu_A^0 + (n_{B,i} - \frac{1}{2}(n_C - n_{C,i})) \mu_B^0 + n_C \mu_C^0 + \sum_i RT n_i \ln\left(\frac{n_i}{n_{TOT}}\right)$$

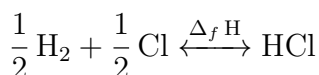
- consider $\text{H}_2 + \text{Cl}_2 \rightleftharpoons 2 \text{HCl}$ at 298 K

$$\mu_{\text{H}_2}^0 = \underbrace{H_{\text{H}_2}^0}_0 - TS_{\text{H}_2}^0 \quad \leftarrow \quad \text{by definition, enthalpy convention of elements}$$

$$\mu_{\text{Cl}_2}^0 = \underbrace{H_{\text{Cl}_2}^0}_0 - TS_{\text{Cl}_2}^0 \quad \leftarrow \quad \text{in their standard state at 298K, 1 atm is set to zero}$$

$$\mu_{\text{HCl}}^0 = \underbrace{H_{\text{HCl}}^0}_0 - TS_{\text{HCl}}^0$$

this is the formation enthalpy for 1 mole of HCl from the elements



Q1) Le Chatelier says that reacting systems “resist” temp. rises by running in endothermic direction

this rxn. is observed to run to left with increasing T , so as written it is exothermic

- van’t Hoff says $\frac{d \ln K_P}{dT} = \frac{\Delta H^0}{RT^2}$

Q2) Using van’t Hoff, if we can estimate $\frac{d \ln K_P}{dT}$, then we can estimate ΔH^0

temp	n_C @ equil	$n_A = n_B$ @ equil	K_P
298K	1.55	0.225	47.5
328K	1.53	0.235	42.5

- using these estimates

$$\Delta \ln K_P = -0.114$$

$$\Delta T = 30K \quad \implies \quad \frac{d \ln K_P}{dT} \approx -0.00379K^{-1}$$

$$\Delta H^0 = RT^2 \frac{d \ln K_P}{dT} \approx -3.09 \text{ kJ}$$

T : use midpoint temp, 313 K; exothermic

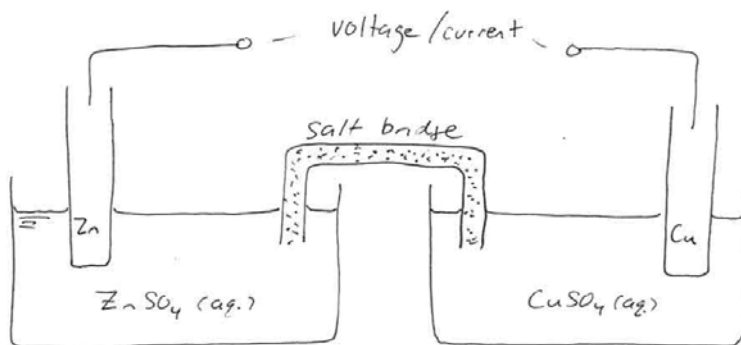
Challenge 1: How do we find temp-dependence of μ_i^0 's?

Challenge 2: Can we estimate ΔC_P from a temperature series of $G'(n_C)$ data?

2 Nernst in a nutshell

- Take a redox reaction
e.g. $\text{Zn} + \text{CuSO}_4 \longleftrightarrow \text{ZnSO}_4 + \text{Cu}$
- Separate reduction & oxidation half-reactions in a device engineered such that electrons and ions follow separate paths

e.g.



- Electrostatic work of moving charge nF across potential \mathcal{E} :

$$-W^* = -\Delta U = \int d\underline{x} \cdot \underline{E}nF = nF\mathcal{E}$$

- n is the moles of fundamental charge, and $F = 96485 \text{ C/mole}$ is Faraday's constant
- \mathcal{E} = electro-motive force (EMF) = potential difference across the cell
- Generalized work theorem

$$\Delta G = W^* \quad \longleftarrow \quad \text{reversible, non-mechanical work}$$

Nernst equation : $\Delta G = -nF\mathcal{E}$

- Use formalism of reacting systems to write ΔG w.r.t. activities/ concentrations

$$\text{e.g. } \Delta G = \Delta G^0 + RT \ln \underbrace{\left(\frac{a_{\text{ZnSO}_4} a_{\text{Cu}}}{a_{\text{CuSO}_4} a_{\text{Zn}}} \right)}_{\text{reaction quotient } Q}$$

- Use Nernst to couple electrostatics to chemistry

$$nF \underbrace{\mathcal{E}}_{\text{cell voltage}} = - \underbrace{\Delta G^0}_{\text{reference}} - RT \ln \underbrace{Q}_{\text{concentrations}}$$

e.g. for Daniell cell, we have

$$\mathcal{E} = \mathcal{E}^0 - \frac{RT}{2F} \ln \frac{[ZnSO_4]}{[CuSO_4]}$$

$[x]$ = concentration in aqueous solution

\mathcal{E}^0 = reference potential for $[ZnSO_4] = [CuSO_4] = 1m$

$n = 2$ because redox reaction involves 2 electrons

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